

isc Silicon NPN Power Transistor

2SD1440

DESCRIPTION

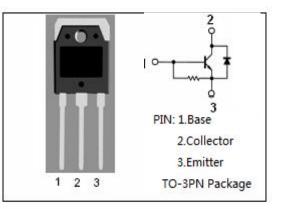
- High Breakdown Voltage-
 - : V_{CBO}= 1500V (Min)
- High Switching Speed
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

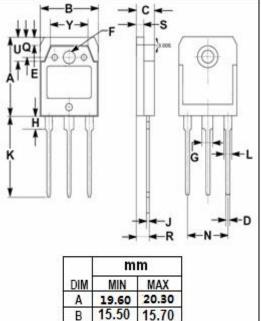
APPLICATIONS

• Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	1500	v	
V _{CES}	Collector-Emitter Voltage	1500	V	
V _{EBO}	Emitter-Base Voltage	5	V	
lc	Collector Current- Continuous	3.5	A	
I _{CP}	Collector Current-Peak	13	A	
Івр	Base Current-Peak	3.5	A	
Pc	Collector Power Dissipation @ T _a = 25°C	2.5	w	
	Collector Power Dissipation @ T _C = 25℃	65		
TJ	Junction Temperature 130		°C	
T _{stg}	Storage Temperature Range	-55~130	°C	





C.111		1117 121
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
Ε	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
Κ	19.80	20.70
L	1.90	2.20
Ν	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

 $T_{\text{c}}\text{=}25^{\circ}\!\!^{\circ}\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 200mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2.5A; I _B = 0.8A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 2.5A; I _B = 0.8A			1.5	V
І _{сво}	Collector Cutoff Current	V _{CB} = 750V; I _E = 0 V _{CB} = 1500V; I _E = 0			50 1.0	μA mA
hfe	DC Current Gain	Ic= 2.5A; Vce= 10V	4		15	
f⊤	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V		2		MHz
V_{ECF}	C-E Diode Forward Voltage	I _F = 4A			2.2	V
ts	Storage Time				9.0	μ S
t _f	Fall Time	I _C = 2.5A, I _{Bend} = 0.8A, L _{leak} = 5 μ Η			0.8	μ S

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